

Session Program

2-6 Jun 2025



3rd DRD3 week on Solid State Detectors R&D

WG6/WP3 - Non-silicon-based detectors

Nikhef, Amsterdam

Thursday 5 June

13:50

WG6/WP3 - Non-silicon-based detectors: Scientific Presentations

Session | Location: Nikhef, Amsterdam

13:50-14:10 Sapphire detector characterization with α -source and e-beam

Speaker

Dr Pietro Grutta

14:10-14:30 Gallium Nitride Schottky Devices for Sensing Applications

Speaker

Christoph Thomas Klein

14:30-14:50

Radiation effects in 4H-SiC PN diodes, LGAD sensors, and MOSFET transistors

Speakers

Jiri Kroll, Radek Novotny

14:50

14:50

WG6/WP3 - Non-silicon-based detectors: Scientific Presentations and WP3 project proposals

Session | Location: Nikhef, Amsterdam

14:50-15:10 Silicon Carbide Source Characterisation Setup and Results at CERN

Speaker

Roman Mueller

15:10-15:30

Characterization of 4H-SiC p-n Junction Detectors for Alpha Particle Detection in Plasma Diagnostics

Speaker

Carmen Torres Munoz

15:30-15:50

Fabrication Progress and Performance Characterization of SiC detectors

Speaker

Xiyuan Zhang

15:50-16:10

Coffee break

16:10-16:30

Development of innovative SiC detectors for harsh environments

Speaker

Dr Giulio Pellegrini

16:30-16:50

In-situ Radiation Damage Study of Silicon Carbide Detectors subjected to Clinical Proton Beams

Speaker

Daniel Radmanovac

16:50-17:10

Mechanisms of proton irradiation-induced defects on the electrical performance of 4H-SiC PIN detectors

Speaker

Zaiyi Li

17:10-17:30

Rising Time and Charge Collection Efficiency of Graphene-Optimized 4H-SiC PIN Detector

Speaker

Congcong Wang

17:30-17:50

Study of 4H-SiC LGADs for 4D-Tracking Application

Speaker

Tao Yang

17:50-18:10

2.5 GeV Proton Irradiated 4H-SiC LGADs

Speaker

Yashas Satapathy

18:10-18:30

Project Proposal disussion and approval

Speakers

Alexander Oh, Dr Tao Yang, Xin Shi

18:30